

RJK2006DPJ, RJK2006DPE, RJK2006DPF

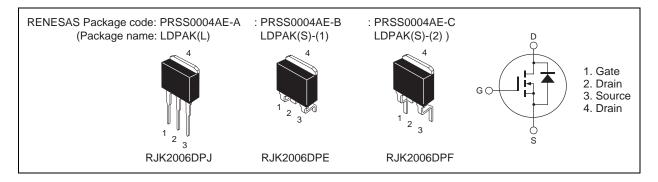
Silicon N Channel MOS FET High Speed Power Switching

REJ03G0512-0200 Rev.2.00 Nov 19, 2009

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source voltage	V _{DSS}	200	V
Gate to Source voltage	V _{GSS}	±30	V
Drain current	I _D	40	А
Drain peak current	I _{D (pulse)} Note1	100	А
Body-Drain diode reverse Drain current	I _{DR}	40	А
Body-Drain diode reverse Drain peak current	I _{DR (pulse)} Note1	100	А
Avalanche current	I _{AP} Note3	27	А
Avalanche energy	E _{AR} Note3	48.6	mJ
Channel dissipation	Pch Note2	100	W
Channel to case thermal impedance	θch-c	1.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

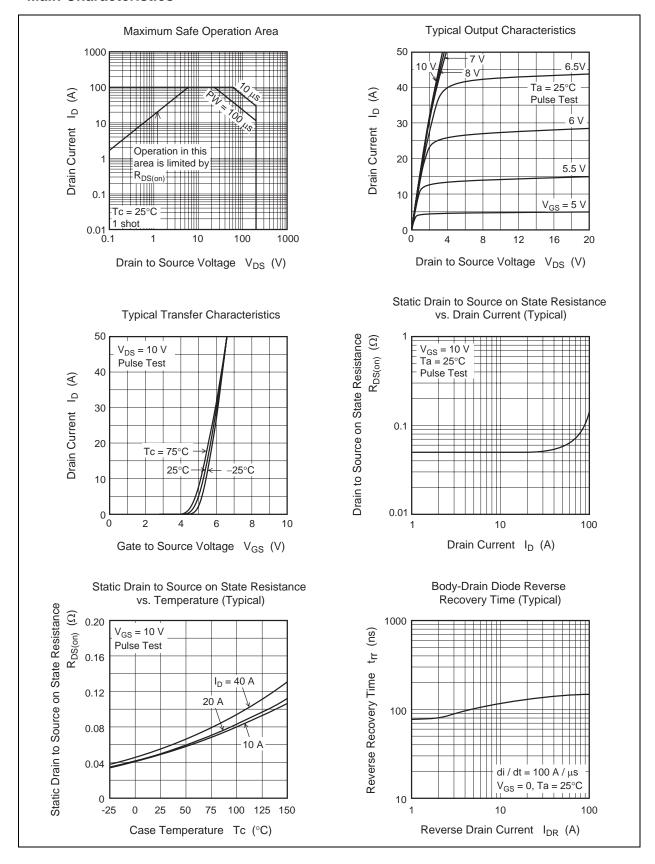
Electrical Characteristics

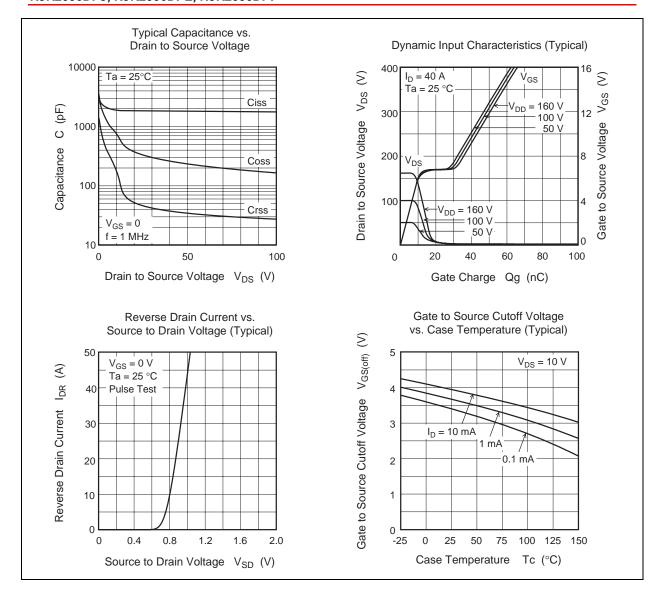
 $(Ta = 25^{\circ}C)$

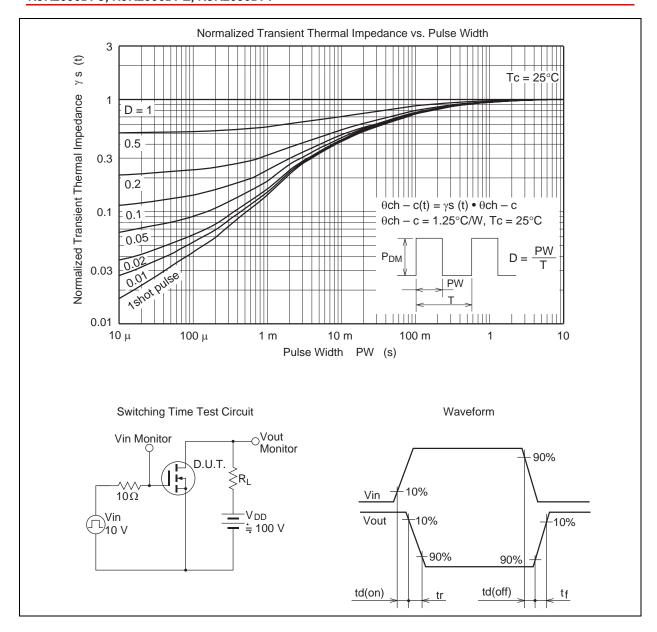
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	200	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero Gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to Source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y _{fs}	15	26	_	S	$I_D = 20 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Static Drain to Source on state resistance	R _{DS(on)}	_	0.052	0.059	Ω	$I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	1800	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	330	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	43	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	30	_	ns	I _D = 20 A
Rise time	t _r	_	180	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	85	_	ns	$R_L = 5 \Omega$
Fall time	t _f	_	100	_	ns	$Rg = 10 \Omega$
Total Gate charge	Qg	_	43	_	nC	V _{DD} = 160 V
Gate to Source charge	Qgs	_	11	_	nC	V _{GS} = 10 V
Gate to Drain charge	Qgd	_	20	_	nC	$I_D = 40 \text{ A}$
Body-Drain diode forward voltage	V_{DF}		1.0	1.5	V	$I_F = 40 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-Drain diode reverse recovery time	t _{rr}	_	150	_	ns	I _F = 40 A, V _{GS} = 0
Body-Drain diode reverse recovery charge	Q _{rr}	_	0.8	_	μС	di _F /dt = 100 A/μs

Notes: 4. Pulse test

Main Characteristics

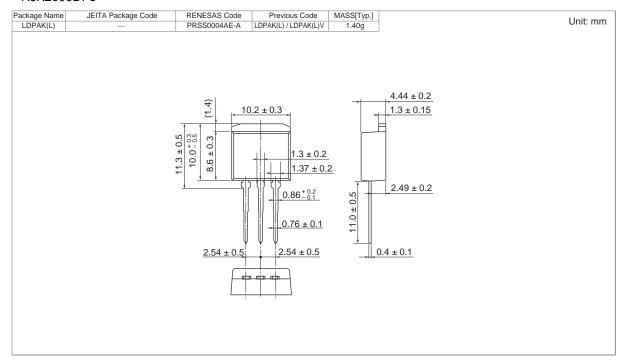




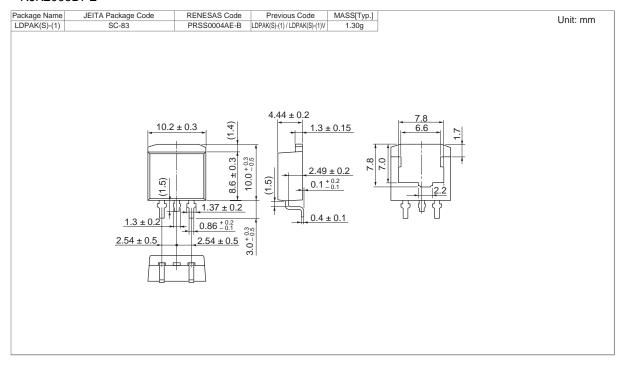


Package Dimensions

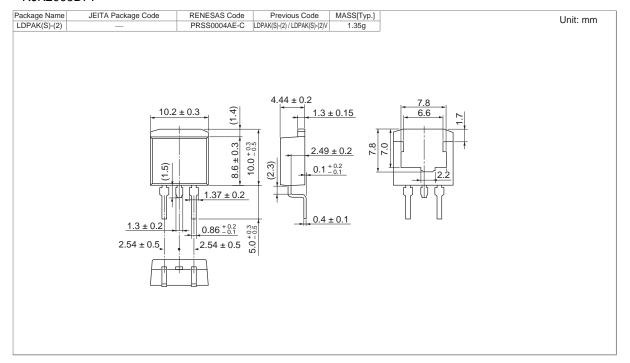
• RJK2006DPJ



• RJK2006DPE



• RJK2006DPF



Ordering Information

Part No.	Quantity	Shipping Container
RJK2006DPE-00-J3	1000 pcs	Taping

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